Switch-mode Dual Schottky Power Rectifier

Features and Benefits

- Highly Stable Oxide Passivated Junction
- Very Low Forward Voltage Drop (0.4 Max @ 10 A, T_C = 150°C)
- High Junction Temperature
- High dv/dt Capability
- Excellent Ability to Withstand Reverse Avalanche Energy Transients
- Low Power Loss/High Efficiency
- High Surge Capacity
- 175°C Operating Junction Temperature
- 20 A Total (10 A Per Diode Leg)
- This Device is Pb-Free and is RoHS Compliant*

Applications

- Power Supply Output Rectification
- Power Management ORING
- Instrumentation

Mechanical Characteristics

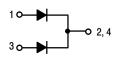
- Case: Epoxy, Molded
- Epoxy Meets UL 94 V-0 @ 0.125 in
- Weight: 1.9 Grams (Approximately)
- Finish: All External Surfaces Corrosion Resistant and Terminal Leads are Readily Solderable
- Lead Temperature for Soldering Purposes: 260°C Max. for 10 Sec
- ESD Rating: Human Body Model 3B Machine Model C



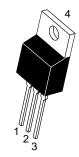
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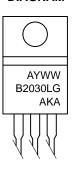
SCHOTTKY BARRIER RECTIFIER 20 AMPERES, 30 VOLTS



MARKING DIAGRAM



TO-220 CASE 221A STYLE 6



A = Assembly Location

Y = Year

WW = Work Week

B2030L = Device Code

G = Pb-Free Package

AKA = Diode Polarity

ORDERING INFORMATION

Device	Package	Shipping
MBR2030CTLG	TO-220 (Pb-Free)	50 Units/Rail

^{*}For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

MAXIMUM RATINGS (Per Leg)

Rating	Symbol	Value	Unit
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage	V _{RRM} V _{RWM} V _R	30	V
Average Rectified Forward Current (T _C = 167°C) Per Diode Per Device	I _{F(AV)}	10 20	A
Non-repetitive Peak Surge Current (Surge applied at rated load conditions halfwave, single phase, 60 Hz)	I _{FSM}	150	А
Peak Repetitive Forward Current (Square Wave, 20 kHz, T _C = 166°C)	I _{FRM}	10	А
Peak Repetitive Reverse Surge Current (2.0 μs, 1.0 kHz)	I _{RRM}	1.0	А
Operating Junction Temperature (Note 1)	TJ	-65 to +175	°C
Storage Temperature	T _{stg}	-65 to +175	°C
Voltage Rate of Change (Rated V _R)	dv/dt	1000	V/μs

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

1. The heat generated must be less than the thermal conductivity from Junction–to–Ambient: $dP_D/dT_J < 1/R_{\theta JA}$.

THERMAL CHARACTERISTICS (Per Leg)

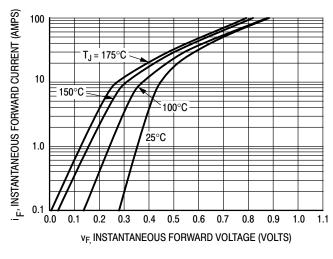
Characteristic	Symbol	Value	Unit
Maximum Thermal Resistance, Junction-to-Case (Min. Pad)	$R_{ heta JC}$	2.0	°C/W
Maximum Thermal Resistance, Junction-to-Ambient (Min. Pad)	$R_{ heta JA}$	60	°C/W

ELECTRICAL CHARACTERISTICS (Per Leg)

Characteristic	Symbol	Min	Тур	Max	Unit
Maximum Instantaneous Forward Voltage (Note 2) ($i_F = 10 \text{ Amps}, T_J = 25^{\circ}\text{C}$) ($i_F = 10 \text{ Amps}, T_J = 150^{\circ}\text{C}$) ($i_F = 20 \text{ Amps}, T_J = 25^{\circ}\text{C}$) ($i_F = 20 \text{ Amps}, T_J = 150^{\circ}\text{C}$)	VF	- - -	0.45 0.32 0.51 0.41	0.52 0.40 0.58 0.48	V
Maximum Instantaneous Reverse Current (Note 2) (Rated dc Voltage, T _J = 25°C) (Rated dc Voltage, T _J = 100°C) (Rated dc Voltage, T _J = 125°C)	i _R	- - -	0.11 10 –	5.0 40 75	mA

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

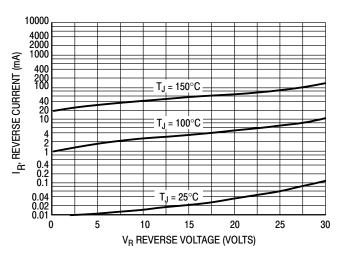
2. Pulse Test: Pulse Width = 5.0 ms, Duty Cycle ≤ 10%.



i F, INSTANTANEOUS FORWARD CURRENT (AMPS) 100 $T_J = 175^{\circ}C$ 10 100°C 150°C 25°C 1.0 0.3 0.4 0.5 0.6 0.7 0.8 0.0 v_{E.} INSTANTANEOUS FORWARD VOLTAGE (VOLTS)

Figure 1. Typical Forward Voltage

Figure 2. Maximum Forward Voltage



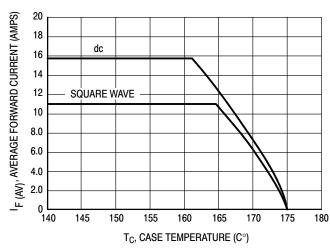
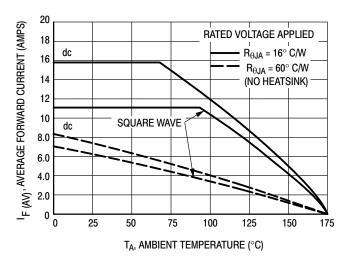


Figure 3. Typical Reverse Current

Figure 4. Current Derating, Case Per Leg



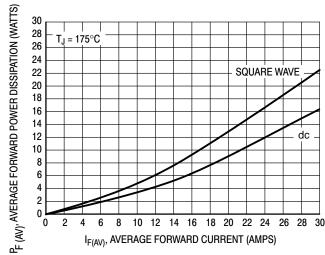


Figure 5. Current Derating, Ambient Per Leg

Figure 6. Forward Power Dissipation

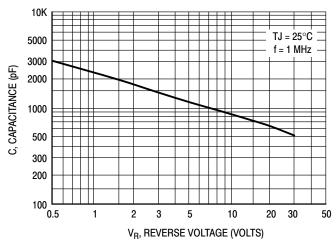
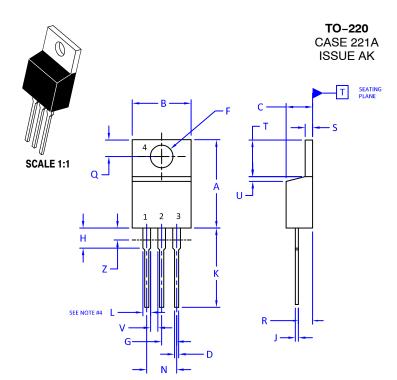


Figure 7. Typical Capacitance





DATE 13 JAN 2022

NOTES:

- 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 2009.
- 2. CONTROLLING DIMENSION: INCHES
- 3. DIMENSION Z DEFINES A ZONE WHERE ALL BODY AND LEAD IRREGULARITIES ARE ALLOWED.

4. MAX WIDTH FOR F102 DEVICE = 1.35MM

	INCHES		MILLIMETERS		
DIM	MIN.	MAX.	MIN.	MAX.	
Α	0.570	0.620	14.48	15.75	
В	0.380	0.415	9.66	10.53	
С	0.160	0.190	4.07	4.83	
D	0.025	0.038	0.64	0.96	
F	0.142	0.161	3.60	4.09	
G	0.095	0.105	2.42	2.66	
Н	0.110	0.161	2.80	4.10	
J	0.014	0.024	0.36	0.61	
К	0.500	0.562	12.70	14.27	
L	0.045	0.060	1.15	1.52	
N	0.190	0.210	4.83	5.33	
Q	0.100	0.120	2.54	3.04	
R	0.080	0.110	2.04	2.79	
S	0.045	0.055	1.15	1.41	
Т	0.235	0.255	5.97	6.47	
U	0.000	0.050	0.00	1.27	
V	0.045		1.15		
Z		0.080		2.04	

STYLE 1: PIN 1. 2. 3. 4.	COLLECTOR EMITTER	STYLE 2: PIN 1. 2. 3. 4.	COLLECTOR	STYLE 3: PIN 1. 2. 3. 4.	ANODE	2. 3.	MAIN TERMINAL 1 MAIN TERMINAL 2 GATE MAIN TERMINAL 2
STYLE 5: PIN 1. 2. 3. 4.	DRAIN SOURCE	STYLE 6: PIN 1. 2. 3. 4.	CATHODE ANODE	STYLE 7: PIN 1. 2. 3. 4.	ANODE	2. 3.	CATHODE ANODE EXTERNAL TRIP/DELAY ANODE
STYLE 9: PIN 1. 2. 3. 4.			GATE SOURCE DRAIN SOURCE	STYLE 11: PIN 1. 2. 3. 4.		STYLE 12: PIN 1. 2. 3. 4.	MAIN TERMINAL 1 MAIN TERMINAL 2 GATE NOT CONNECTED

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